EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		(436/174.ccls.).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/29 15:24
L1	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and thrid and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness and slant)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:28
L2	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and thrid and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness and slant)"clm."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:28

L3	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and thrid and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness)"clm."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:28
L4	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness)"clm."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:28
L5	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness and slant)"clm."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:28

L6	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness and slant).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:29
L7	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:29
L8	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:29

L9	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:29
L10	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:29
L11	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:33

L12	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:33
L13	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:33
L14	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:33
L15	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:34

L16	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:34
L17	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:34
L18	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:34
L19	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:34
L20	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:35

L21	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:35
L22	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:35
L23	1	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:35
L51	1	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:41
L52	1	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:41
L53	1	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:41
L54	1	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:41
L55	1	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:41

L56	1	(method and making and lamina and sample and forming and lamina and etching).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:41
L57	1	(method and making and lamina and sample and forming).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:42
L58	3	(method and making and lamina and sample).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2009/11/12 13:42
S1	1435	436/174.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 15:25
S2	69	S1 and (ion near1 source)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 15:25
S3	0	S1 and (lamina and sputtering)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 15:28
S4	4	(lamina and sputtering).ab.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 15:28
S5	1623174	(lamina and ion source).ab.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 15:40
S6	2	(lamina and (ion near1 source)).ab.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 15:40

S7	11	"6193199"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 15:43
S8	3	"6897665"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 16:13
S9	0	"FUJII-T.in. "	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 16:48
S10	107872	FUJII.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 16:48
S11	3	S10 and semicondcutor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 16:50
S12	7664	S10 and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 16:50
S13	1678	S12 and (focused ion beam)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 16:51
S14	1040	S13 and (second near5 ion beam)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 16:55
S15	1	S14 and (plural near2 drive near2 shafts)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 16:56

S16	1	S12 and (plural near2 drive near2 shafts)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/29 16:57
S17	2	"7276691"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 15:59
S18	5	("20020017619" | "20050236587" | "5525806" | "5574280" | "6838685").PN. OR ("7276691").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/04 16:00
S19	18488	sharp.as.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/04 16:36
S20	203374	sharp.as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 16:36
S21	7	S20 and lamina	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 16:36
S22	289932	microscope	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 16:38
S23	12423	S22 and (ion near1 beam)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 16:38
S24	44	S23 and lamina	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 16:38

S25	2	"7223480"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 16:58
S26	5	"6786978"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 16:59
S27	2	tashiaki.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 17:07
S28	94953	toshiaki.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 17:07
S29	0	S27 and beam	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 17:07
S30	4421	S28 and beam	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 17:07
S31	480	S30 and (laminated or laminating or lamina)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 17:08
S32	156	S31 and stage	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 17:08
S33	31	S32 and microscope	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/04 17:08

S34	3	("2006/0157341").URPN.	USPAT	OR	OFF	2009/05/04 17:10
S35	2204	sii.as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 15:33
S36	2206	sii.as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/06 15:33
S37	54	S36 and composite	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/06 15:34
S38	28	"5574280"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/06 15:38
S39	1556	436/174.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/07 11:05
S40	1556	436/174.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/07 11:06
S41	32	S40 and ion near1 beam	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/05/07 11:06

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp

L24	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and thrid and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness and slant)	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:35
L36	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness and slant)	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:37
L37	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness and slant).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:37

L38	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined and thickness).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:38
L39	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low and predetermined).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:39
L40	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing and low).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:39

L41	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope and observing).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:39
L42	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region and microscope).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:39
L43	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall and region).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:39
L44	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side and wall).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:39

L45	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing and side).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:39
L46	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region and exposing).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:40
L47	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked and region).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:40
L48	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working and worked).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:40
L49	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process and sputtering-etching-working).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:40

L50	0	(method and making and lamina and sample and forming and lamina and etching and scan-irradiating and focused and ion and beam and sample and surface and first and second and third and fourth and process).clm.	US-PGPUB; USPAT; UPAD	AND	OFF	2009/11/12 13:40

11/12/2009 1:43:19 PM
C:\Documents and Settings\bramdhanie\My Documents\EAST\Workspaces\10563515.wsp